

NGD8201AN

Ignition IGBT

20 A, 400 V, N-Channel DPAK

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Overvoltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

Features

- Ideal for Coil-on-Plug and Driver-on-Coil Applications
- DPAK Package Offers Smaller Footprint for Increased Board Space
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage for Interfacing Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- These are Pb-Free Devices

Applications

- Ignition Systems

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	440	V
Collector-Gate Voltage	V_{CER}	440	V
Gate-Emitter Voltage	V_{GE}	± 15	V
Collector Current-Continuous @ $T_C = 25^\circ\text{C}$ - Pulsed	I_C	20 50	A_{DC} A_{AC}
Continuous Gate Current	I_G	1.0	mA
Transient Gate Current ($t \leq 2$ ms, $f \leq 100$ Hz)	I_G	20	mA
ESD (Charged-Device Model)	ESD	2.0	kV
ESD (Human Body Model) $R = 1500 \Omega$, $C = 100$ pF	ESD	8.0	kV
ESD (Machine Model) $R = 0 \Omega$, $C = 200$ pF	ESD	500	V
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	125 0.83	W W/ $^\circ\text{C}$
Operating & Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

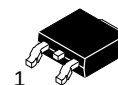
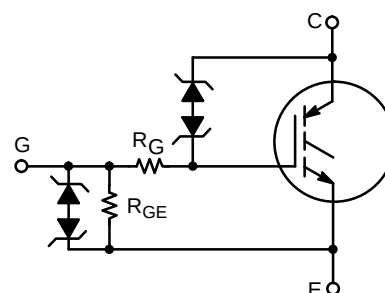


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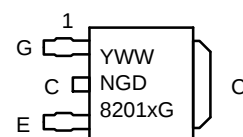
20 A, 400 V

$V_{CE(on)} = 1.3 \text{ V @}$
 $I_C = 10 \text{ A, } V_{GE} \geq 4.5 \text{ V}$



DPAK
CASE 369C
STYLE 7

MARKING DIAGRAM



Y = Year
WW = Work Week
NGD8201x = Device Code
x = A
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGD8201ANT4G	DPAK (Pb-Free)	2500 / Tape & Reel

NGD8201AN

UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS ($-55^{\circ} \leq T_J \leq 175^{\circ}C$)

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $Pk\ I_L = 16.7\text{ A}$, $R_G = 1000\ \Omega$, $L = 1.8\text{ mH}$, Starting $T_J = 25^{\circ}C$ $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $Pk\ I_L = 14.9\text{ A}$, $R_G = 1000\ \Omega$, $L = 1.8\text{ mH}$, Starting $T_J = 150^{\circ}C$ $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $Pk\ I_L = 14.1\text{ A}$, $R_G = 1000\ \Omega$, $L = 1.8\text{ mH}$, Starting $T_J = 175^{\circ}C$	E_{AS}	250 200 180	mJ
Reverse Avalanche Energy $V_{CC} = 100\text{ V}$, $V_{GE} = 20\text{ V}$, $Pk\ I_L = 25.8\text{ A}$, $L = 6.0\text{ mH}$, Starting $T_J = 25^{\circ}C$	$E_{AS(R)}$	2000	mJ

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.2	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	95	$^{\circ}C/W$
Maximum Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	275	$^{\circ}C$

1. When surface mounted to an FR4 board using the minimum recommended pad size (76x76x1.6mm board size, 60 sqmm 1 oz. Copper).

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Clamp Voltage	BV_{CES}	$I_C = 2.0\text{ mA}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	370	395	420	V
		$I_C = 10\text{ mA}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	390	415	440	
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 15\text{ V}$	$T_J = 25^{\circ}C$		0.1	1.0	μA
			$T_J = 175^{\circ}C$	0.5	1.5	10	
		$V_{CE} = 200\text{ V}$, $V_{GE} = 0\text{ V}$	$T_J = 175^{\circ}C$	1.0	25	100*	μA
			$T_J = -40^{\circ}C$	0.4	0.8	5.0	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75\text{ mA}$	$T_J = 25^{\circ}C$	30	35	39	V
			$T_J = 175^{\circ}C$	35	39	45*	
			$T_J = -40^{\circ}C$	30	33	37	
Reverse Collector-Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24\text{ V}$	$T_J = 25^{\circ}C$	0.05	0.2	1.0	mA
			$T_J = 175^{\circ}C$	1.0	8.5	25	
			$T_J = -40^{\circ}C$	0.005	0.025	0.2	
Gate-Emitter Clamp Voltage	BV_{GES}	$I_G = \pm 5.0\text{ mA}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	12	12.5	14	V
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 5.0\text{ V}$	$T_J = -40^{\circ}C$ to $175^{\circ}C$	200	300	350*	μA
Gate Resistor	R_G		$T_J = -40^{\circ}C$ to $175^{\circ}C$		70		Ω
Gate-Emitter Resistor	R_{GE}		$T_J = -40^{\circ}C$ to $175^{\circ}C$	14.25	16	25	k Ω

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0\text{ mA}$, $V_{GE} = V_{CE}$	$T_J = 25^{\circ}C$	1.5	1.8	2.1	V
			$T_J = 175^{\circ}C$	0.7	1.0	1.3	
			$T_J = -40^{\circ}C$	1.7	2.0	2.3*	
Threshold Temperature Coefficient (Negative)				4.0	4.6	5.2	mV/ $^{\circ}C$

*Maximum Value of Characteristic across Temperature Range.

3. Pulse Test: Pulse Width $\leq 300\ \mu S$, Duty Cycle $\leq 2\%$.